

# Design of a Segmented LGAD Sensor for Development of 4-D Tracking Detector

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## 4D Tracker

Should we add time information to the hits,

- Identify vertices otherwise difficult using position information only
- Effective in forward regions where vertexing precision is limited

( $\Delta t=10\text{ps} \Leftrightarrow \Delta z=3\text{mm}$ )

collision points

Position

Time

Adding time information

central forward

Tracks reconstructed by ATLAS (event with 17 interactions)

Expect 200/crossing at HL-LHC

hits

Adding time information

Should we add time information to each hit,

- Reconstruct tracks using proper time differences
- Help reduce wrong hit combinations and effective in reducing the track reconstruction CPU

→ Innovation in tracking

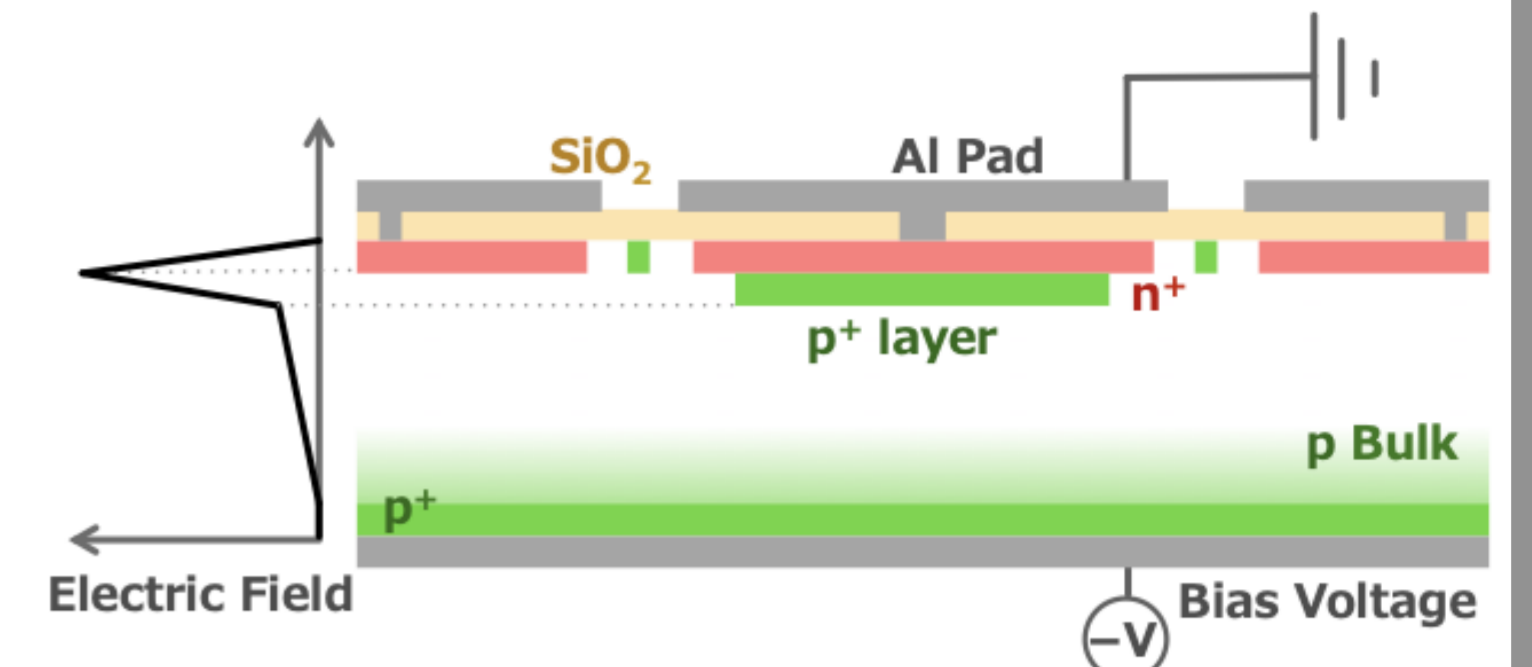
## Low-Gain Avalanche Detector (LGAD)

Add p<sup>+</sup> layer underneath the n<sup>+</sup> readout electrode  
High E-field induces avalanche multiplication

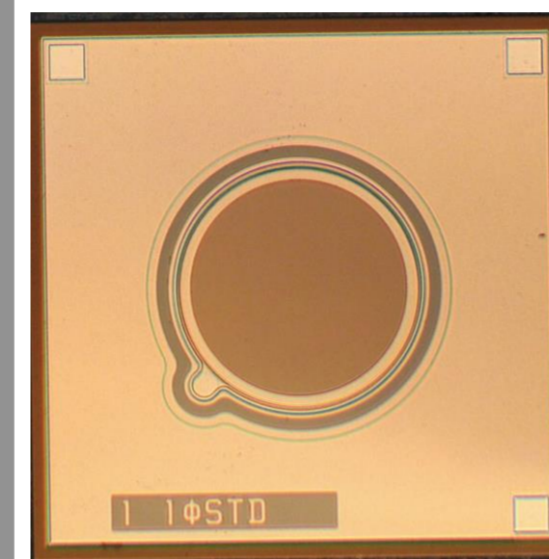
- thin (50 $\mu\text{m}$ ) substrate is effective for signal creation
- short charge collection time with fast signal shape

→ good time resolution O(10ps)

with superior position resolution O(10 $\mu\text{m}$ ) achievable with semiconductor, LGAD is a good candidate for realizing 4-D tracker.



## HPK LGAD samples



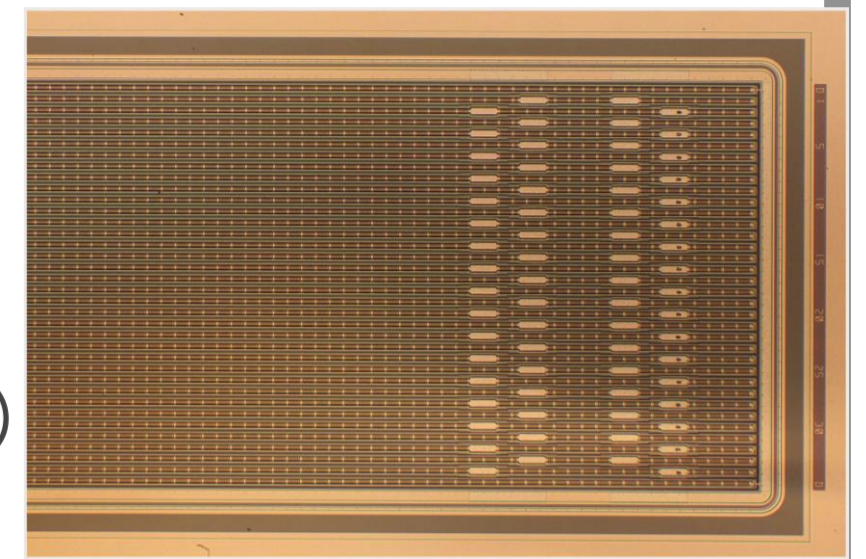
### Pad type

window : 1mmD

Active thickness : 50 or 80 $\mu\text{m}$  (150 $\mu\text{m}$  physical)  
p<sup>+</sup> layer concentration : 4 steps (A<B<C<D)

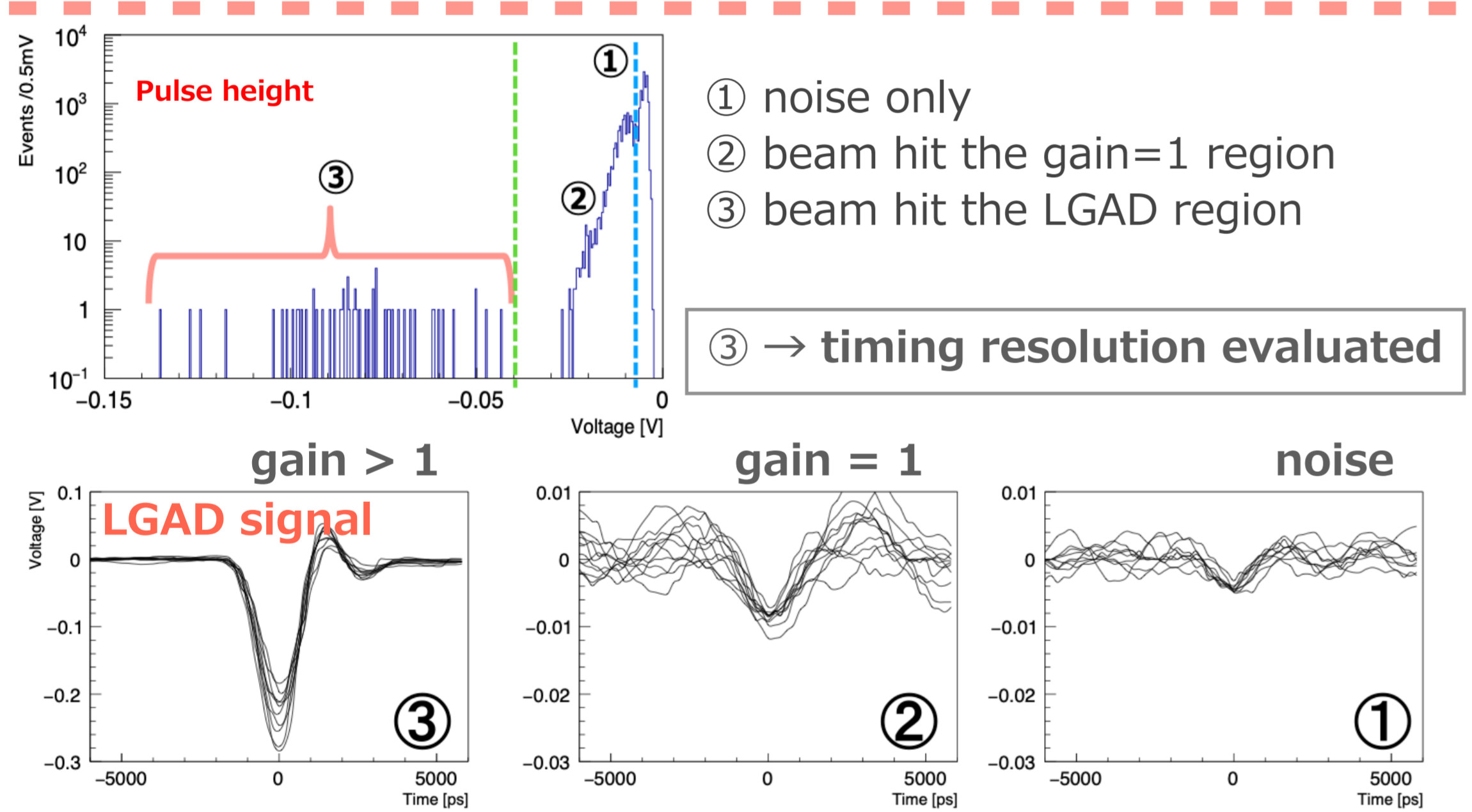
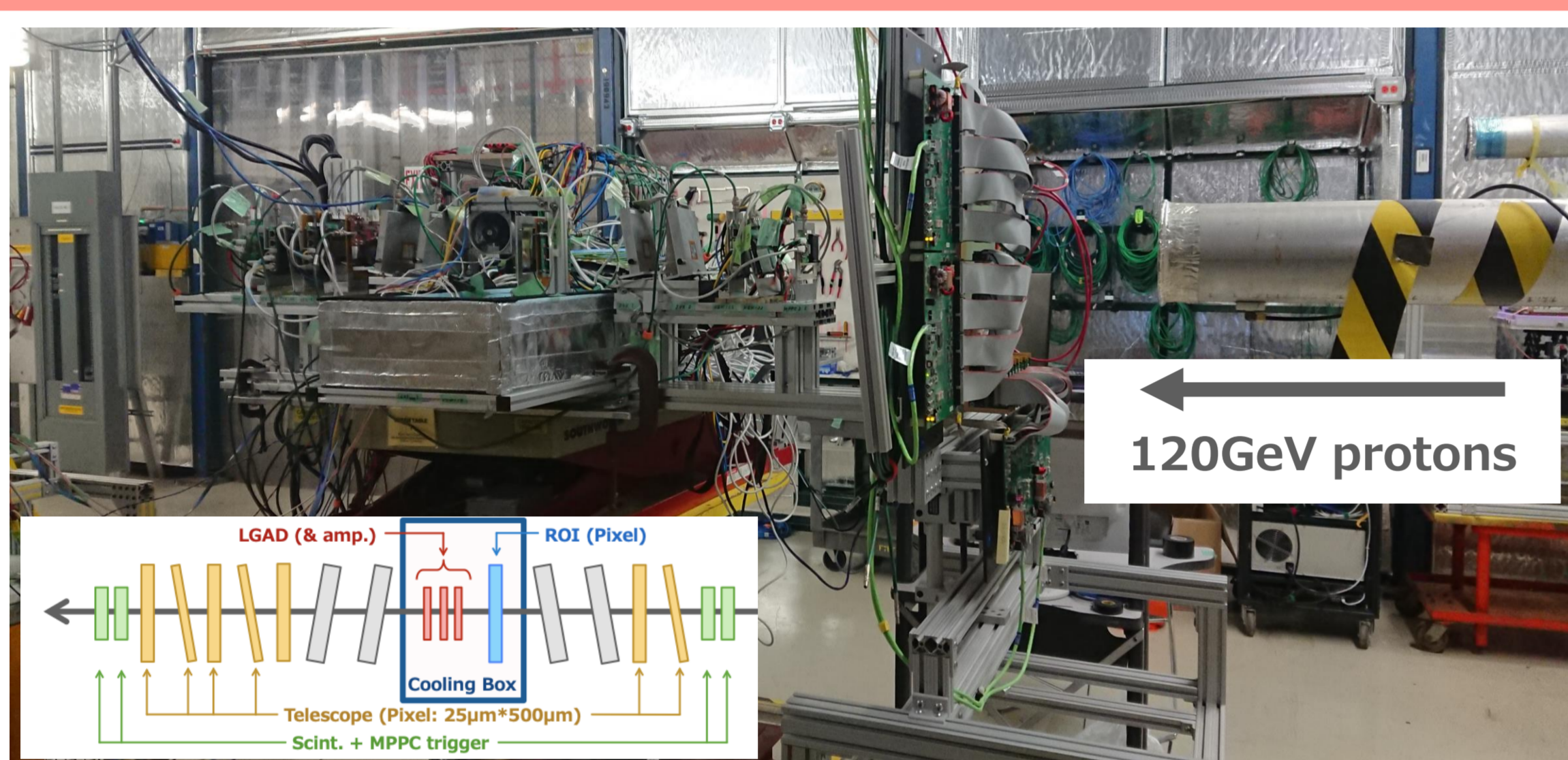
### Strip type

strip pitch : 80 $\mu\text{m}$

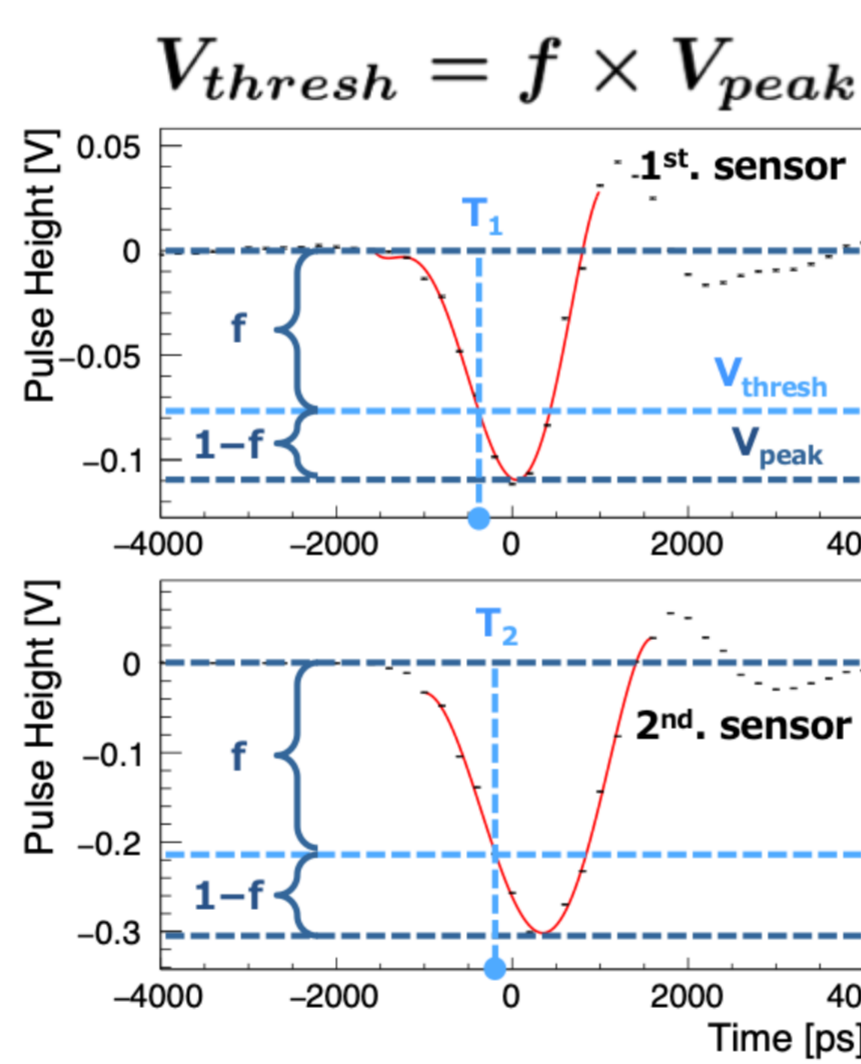


## Evaluation of Timing Precision in High-Energy Beam

Feb 20-Mar 4, 2018 @FNAL FTBF



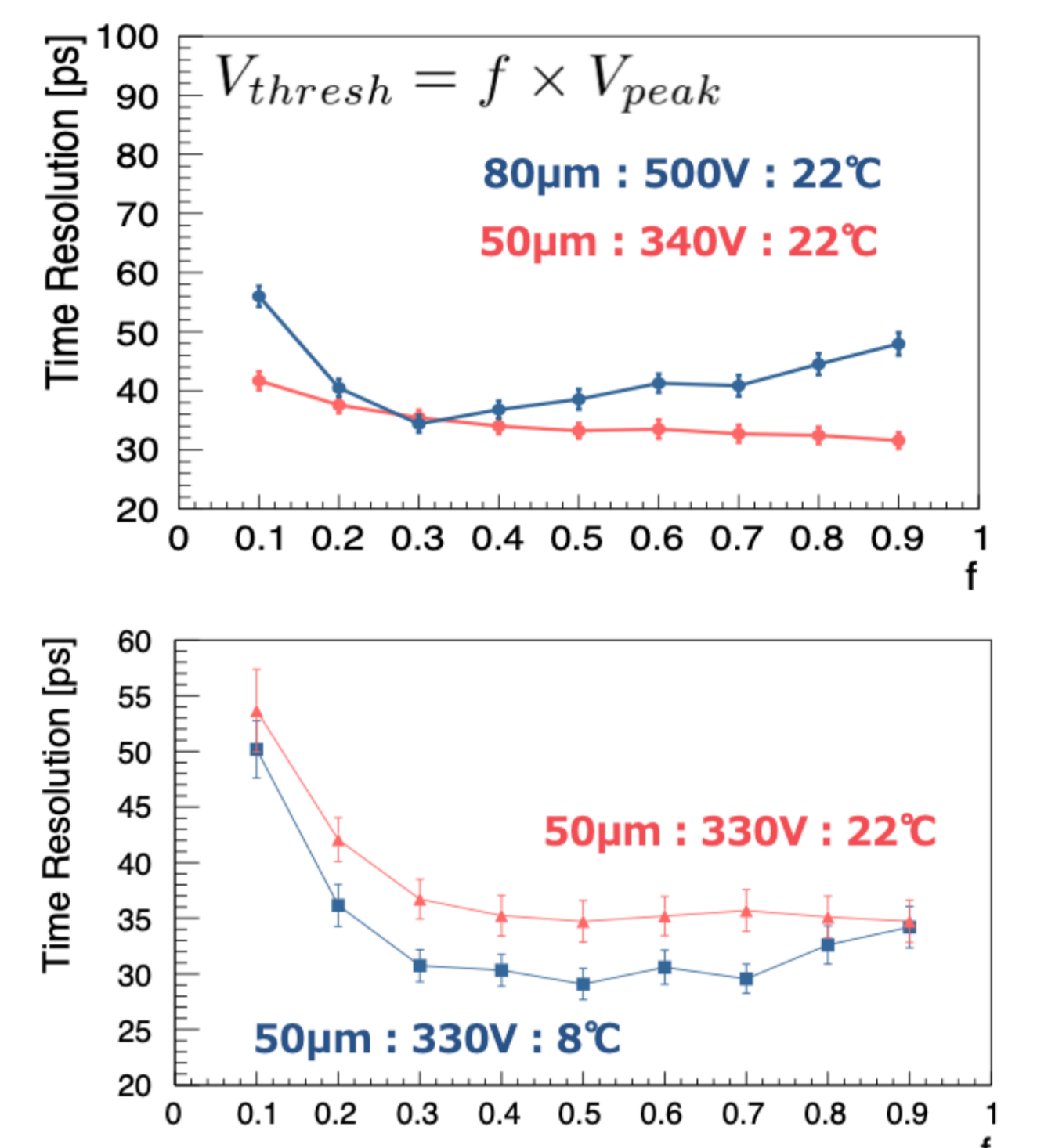
## evaluation



## Signal readout

LGAD signal is amplified (using high-speed amps) and digitized using DRS4 flash ADCs (5GS/s)

- Pulse height : 12bit, 1Vpp (1V/4096 ~ 0.25mV)
- Time bins : 10bit, 5GS/s (200ps\*1024~200ns F.S.)

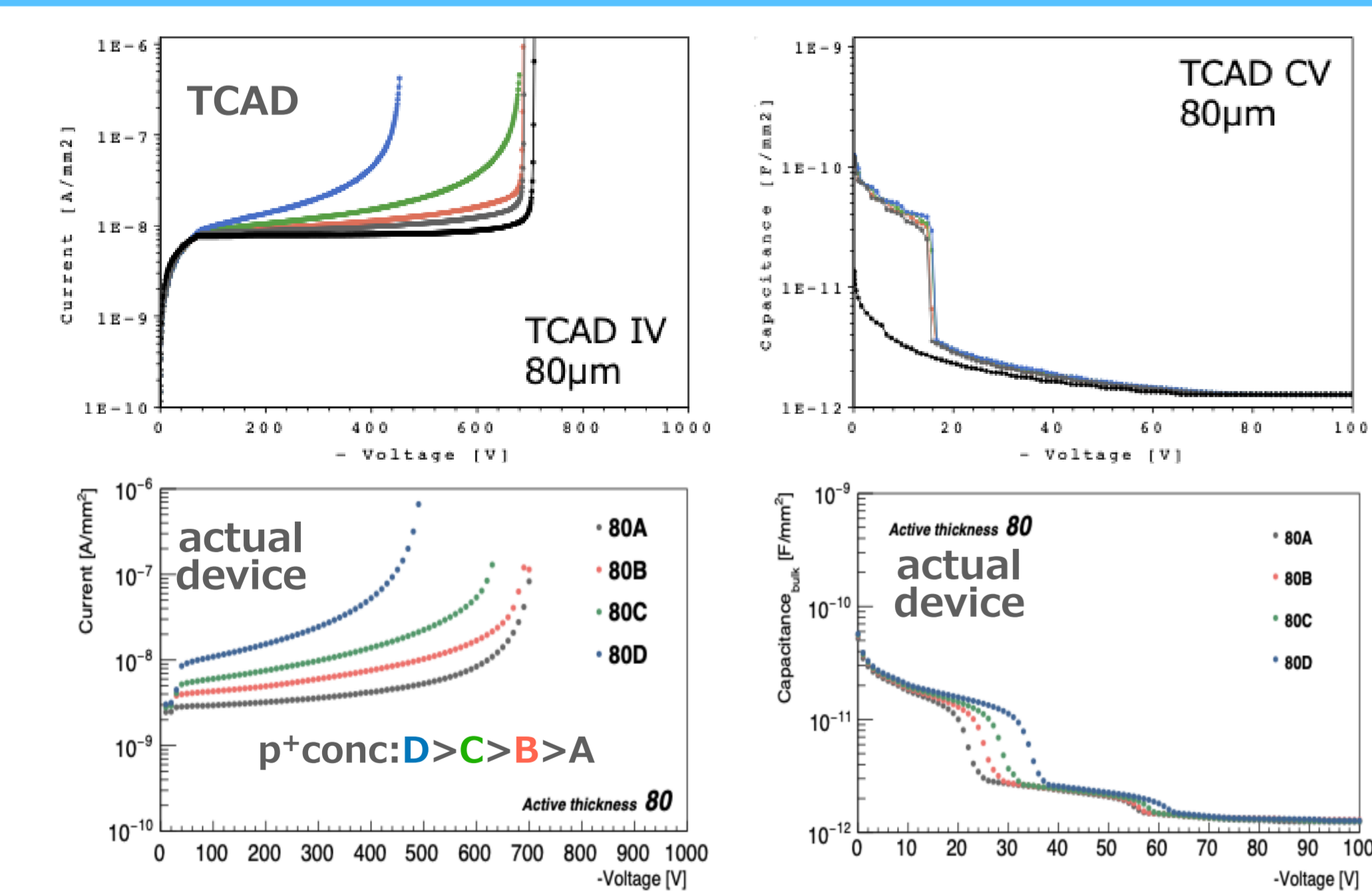


## results

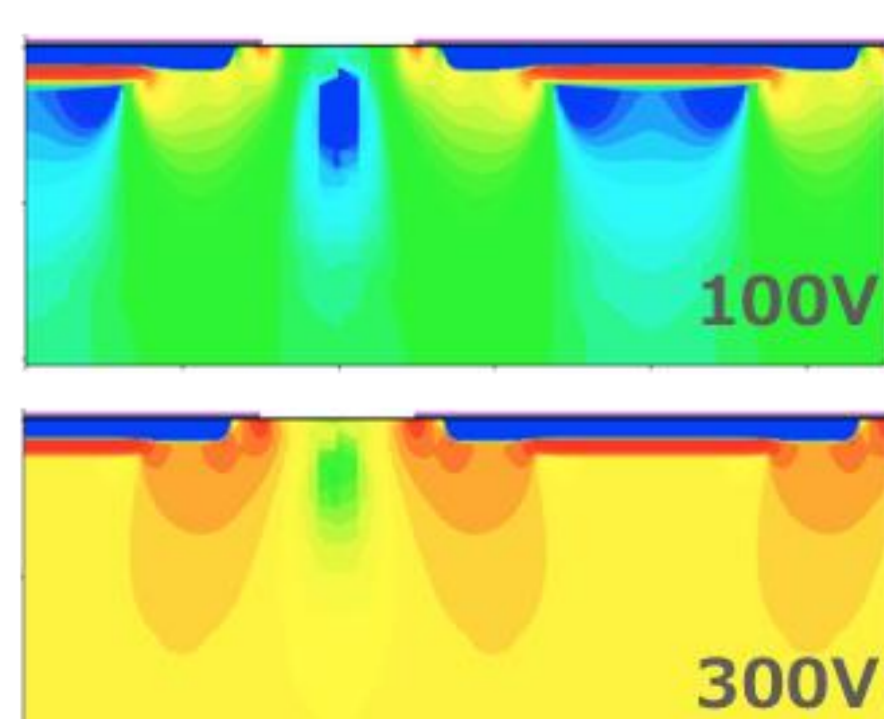
- Better timing precision achieved
- for thinner active thickness
    - 50 $\mu\text{m}$  : ~30ps @340V (f=0.9)
    - 80 $\mu\text{m}$  : ~40ps @500V (f=0.3)
  - at lower temperature
    - 22 $^{\circ}\text{C}$  : ~35ps @330V (f=0.5)
    - 8 $^{\circ}\text{C}$  : ~28ps @330V (f=0.5)
- as expected for higher LGAD gain

## TCAD Simulation for Segmented LGADs

TCAD Sentaurus™ (synopsys)

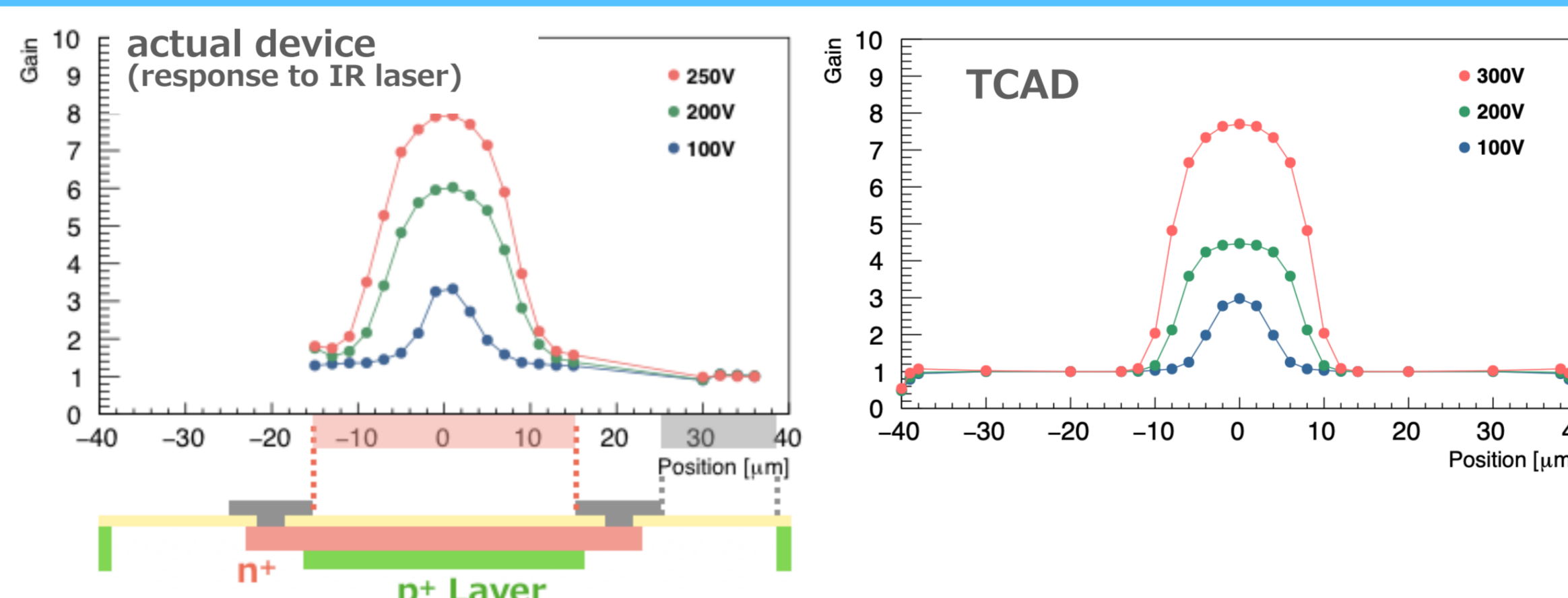


Measured IV and CV are reproduced by TCAD at a precision reasonably well



at 100V, E-field in the junction is not high and multiplication is not large.

at 300V, E-field in the junction is high but too large at the ends of the multiplication layers, causing sensor breakdown.

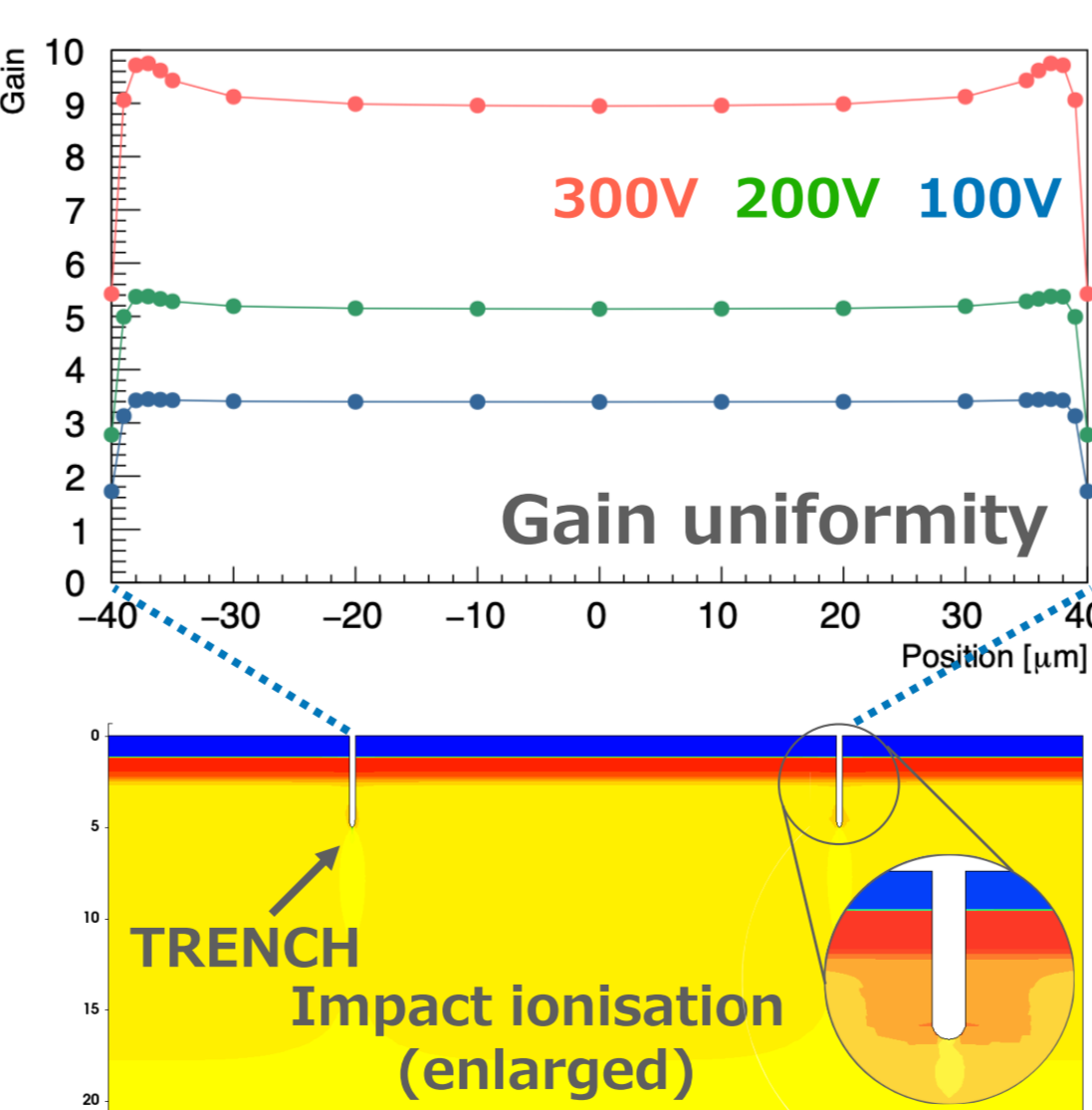


Gain non-uniformity of strip is also reproduced by TCAD

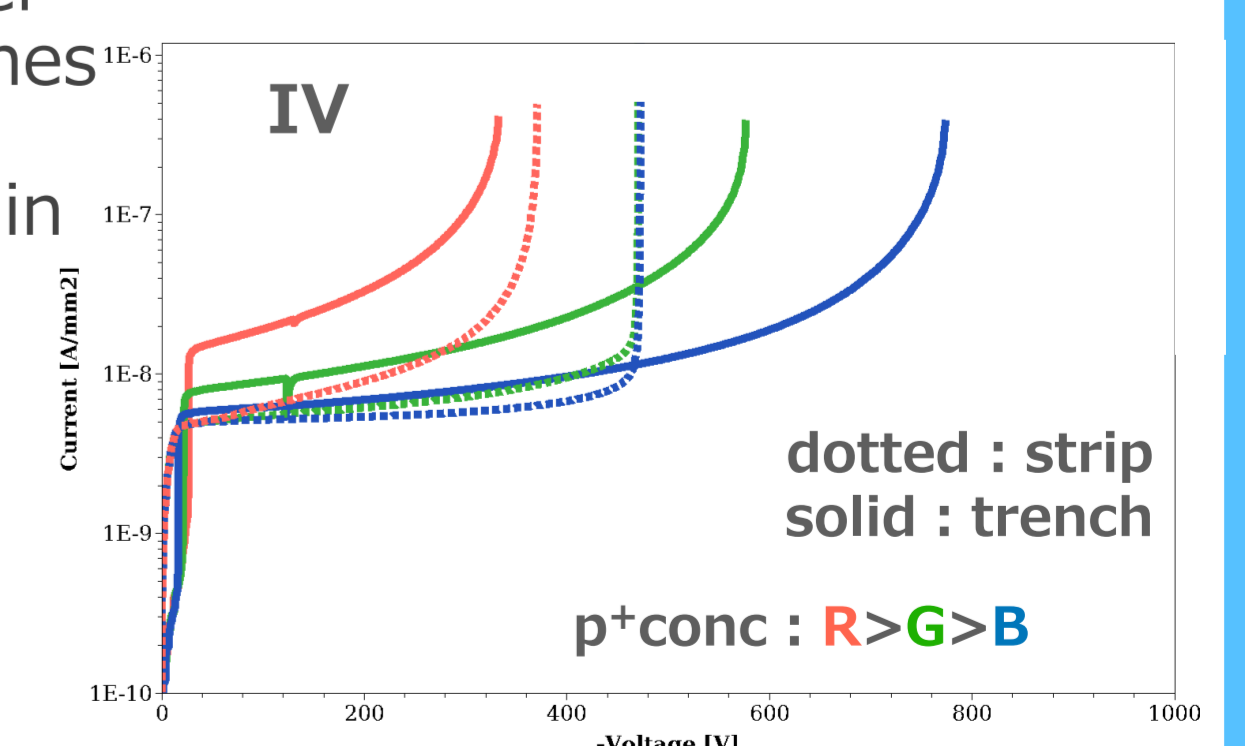
TCAD with parameters tuned to reproduce the measurements is used to simulate new segmented devices with least non-uniformity

## candidate : deep trench

To separate electrodes physical by deep and thin trenches



- Uniform gain~10 is obtainable in wider region except a few  $\mu\text{m}$  around trenches
- IV characteristics is more stable than in the strip type
- E-field concentration around the trenches causes the breakdown. Needs optimization of neutralisation process around the trenches



→ trench is a good candidate for the LGAD segmentation, but need further process optimisation

## Summary

- We are developing LGAD sensors to realise 4-D tracking detector
- Time precision better than 30 ps is obtained from test beam measurements
- TCAD simulation tuned to reproduce measured characteristics is used to design segmented LGAD sensors. Trench is a good candidate. Continue to optimize the electrode structure and trench process

## Acknowledgement

